

Title (en)

A semiconductor memory device with information loss self-detect capability

Title (de)

Halbleiterspeicheranordnung mit Fähigkeit zur Informationsverlusterkennung

Title (fr)

Dispositif de mémoire à semi-conducteurs avec la capacité de détection de perte d'information

Publication

**EP 1717817 B8 20160518 (EN)**

Application

**EP 05103557 A 20050429**

Priority

EP 05103557 A 20050429

Abstract (en)

[origin: EP1717817A1] A semiconductor memory device ( 100 ), including a plurality of programmable memory cells ( MC ) each one adapted to be brought into one among at least a first status and a second status, said plurality of memory cells including memory cells intended to store data, and means for accessing ( 115,130,135 ) the memory cells for reading/modifying their status. At least one memory cell ( FMC ) in said plurality is used as detector memory cell, and control means ( 145 ) operatively associated with the at least one detector memory cell are provided, said control means being adapted to establishing a potential loss of the data stored in the memory cells of said plurality based on a detected first status of the at least one detector memory cell.

IPC 8 full level

**G11C 13/00** (2006.01); **G11C 16/34** (2006.01)

CPC (source: EP US)

**G11C 11/22** (2013.01 - EP US); **G11C 11/2275** (2013.01 - EP US); **G11C 13/0004** (2013.01 - EP US); **G11C 13/0033** (2013.01 - EP US); **G11C 13/0069** (2013.01 - EP US); **G11C 16/3431** (2013.01 - EP US); **G11C 2013/0083** (2013.01 - EP US)

Cited by

EP1933327A3; EP1927990A3; EP1858021A3; CN102369579A; US7539050B2; WO2019059970A1; US7460394B2; US10319437B2; JP2008152904A; WO2007145710A1; WO2010076826A1

Designated contracting state (EPC)

DE FR GB IT

DOCDB simple family (publication)

**EP 1717817 A1 20061102**; **EP 1717817 B1 20160413**; **EP 1717817 B8 20160518**; US 2007253238 A1 20071101; US 7414902 B2 20080819

DOCDB simple family (application)

**EP 05103557 A 20050429**; US 41587906 A 20060501